优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
40V	4.5mΩ @ V_{GS} = 10V	95A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses

Description and Applications

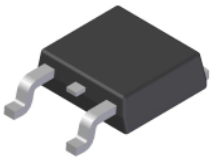
This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

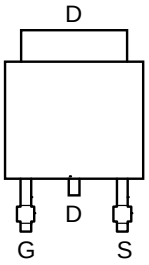
Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

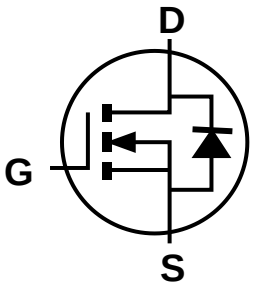
TO252 (DPAK)



Top View



Top View
Pin Out



Internal Schematic

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6)	T_C = +25°C (Note 9)	I_D	95	A
	T_C = +100°C		73	
Maximum Body Diode Forward Current (Note 6)	T_C = +25°C	I_S	83	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	150	A
Avalanche Current, L=0.1mH		I_{AS}	32.5	A
Avalanche Energy, L=0.1mH		E_{AS}	52.8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	38	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	100	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.6	4.5	mΩ	V_{GS} = 10V, I_D = 50A
Diode Forward Voltage	V_{SD}	—	0.9	—	V	V_{GS} = 0V, I_S = 50A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	3,062	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	902.2	—		
Reverse Transfer Capacitance	C_{rss}	—	179.2	—		
Gate Resistance	R_G	—	0.67	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	49.1	—	nC	V_{DD} = 20V, I_D = 50A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	10.3	—		
Gate-Drain Charge	Q_{gd}	—	13	—		
Turn-On Delay Time	$t_{D(ON)}$	—	8.7	—	ns	V_{DD} = 20V, V_{GS} = 10V, I_D = 50A, R_G = 3Ω
Turn-On Rise Time	t_R	—	6.8	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	18.6	—		
Turn-Off Fall Time	t_F	—	7.3	—		
Body Diode Reverse Recovery Time	t_{RR}	—	31.8	—	ns	I_F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	26.5	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.
9. Package limited.

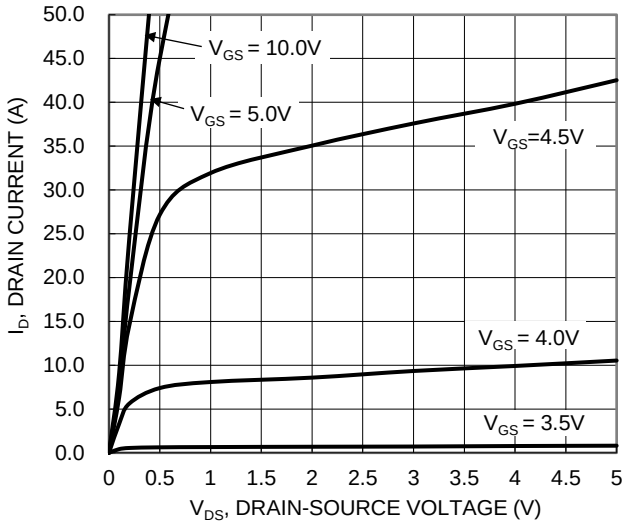


Figure 1. Typical Output Characteristic

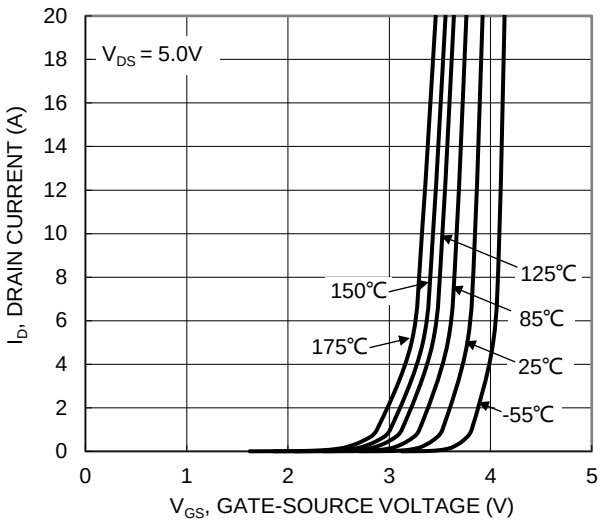


Figure 2. Typical Transfer Characteristic

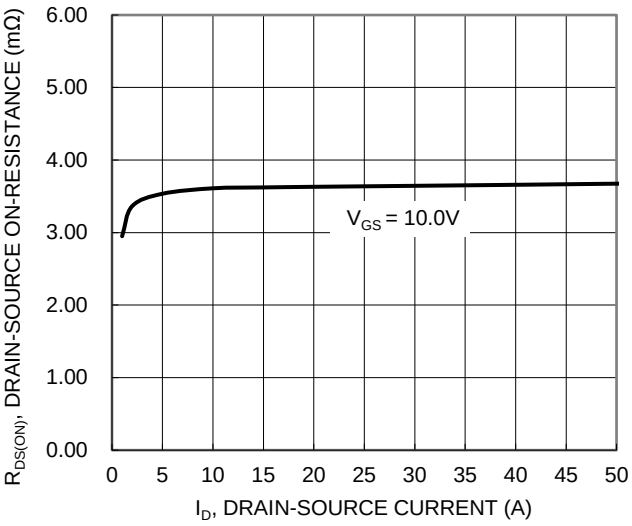


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

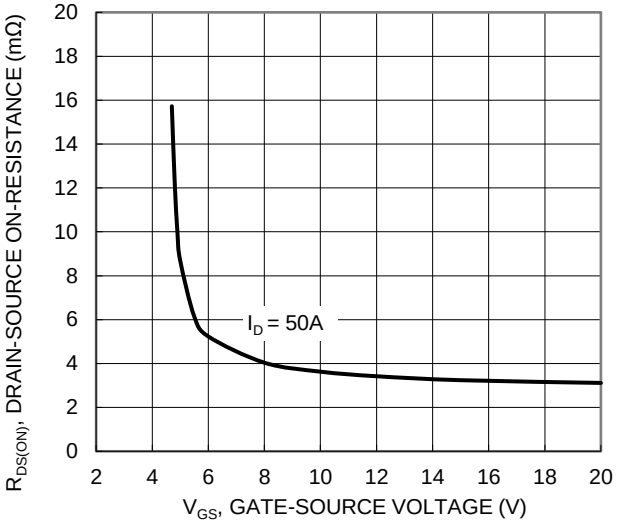


Figure 4. Typical Transfer Characteristic

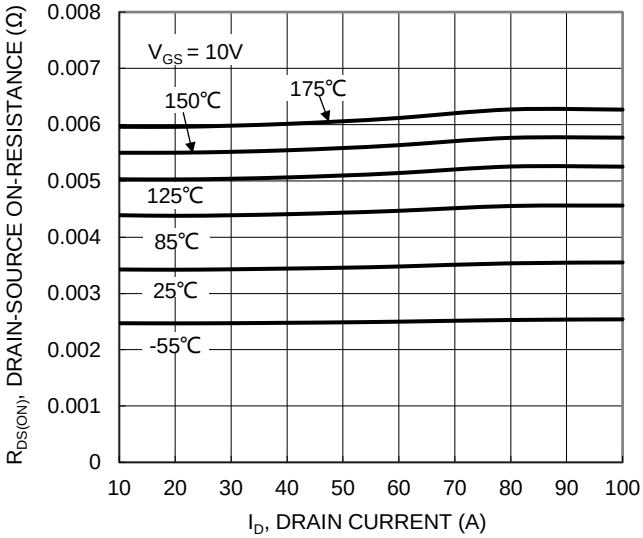


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

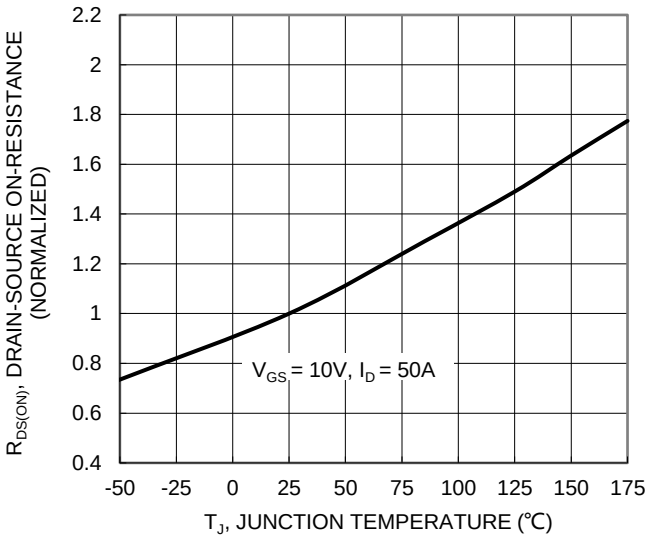


Figure 6. On-Resistance Variation with Temperature

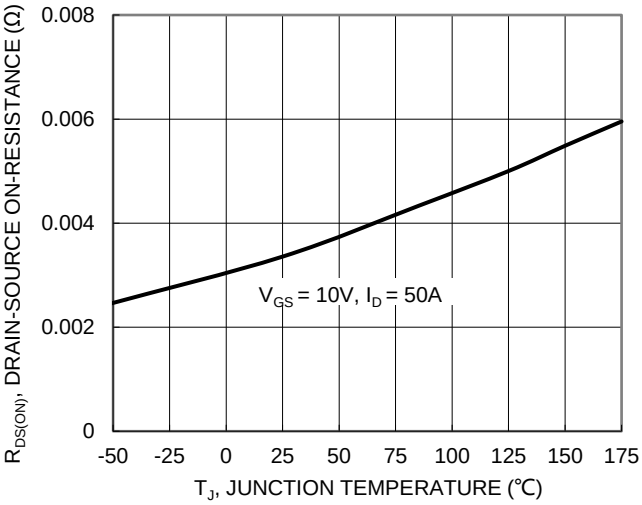


Figure 7. On-Resistance Variation with Temperature

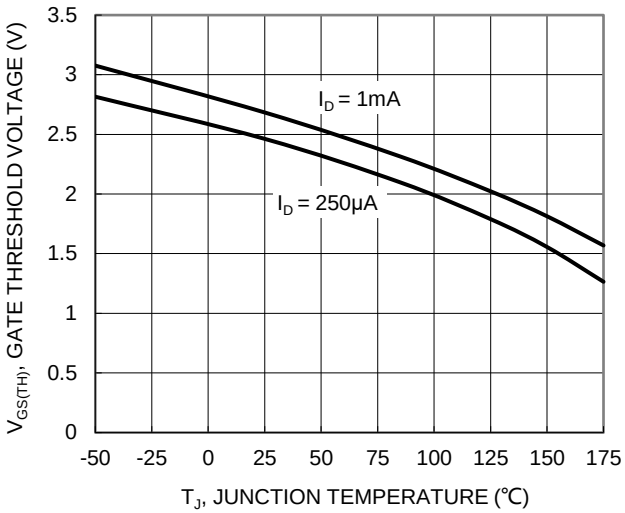


Figure 8. Gate Threshold Variation vs. Temperature

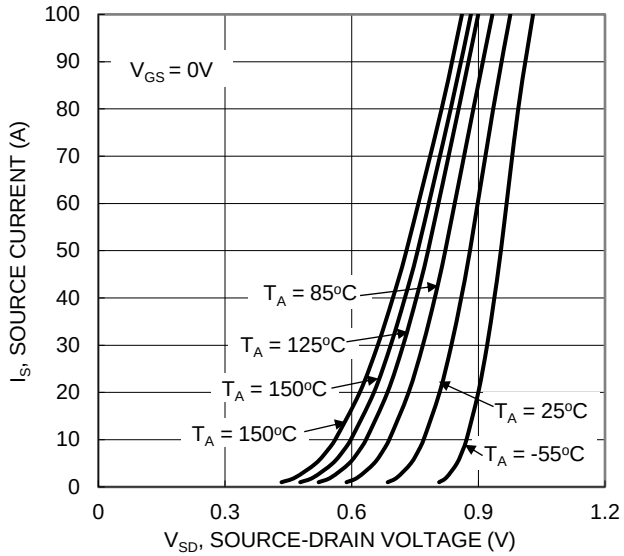


Figure 9. Diode Forward Voltage vs. Current

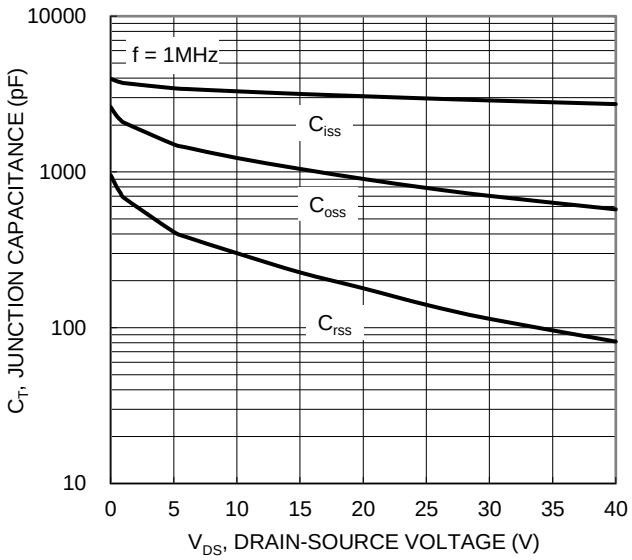


Figure 10. Typical Junction Capacitance

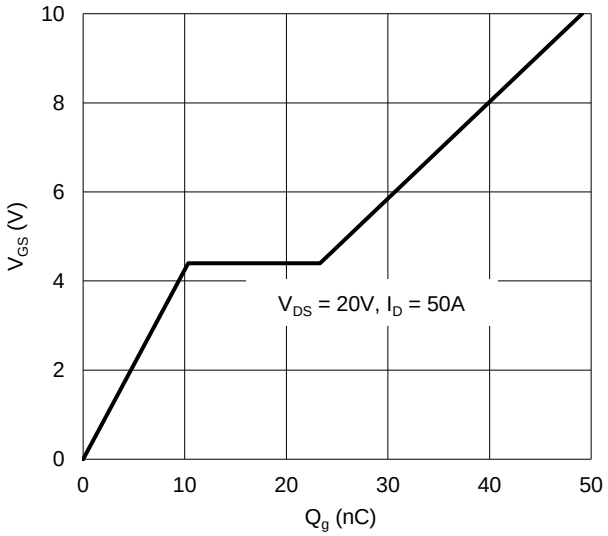


Figure 11. Gate Charge

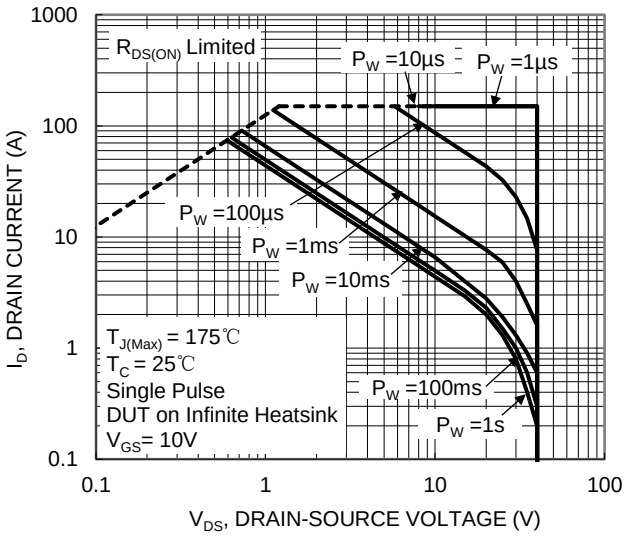


Figure 12. SOA, Safe Operation Area

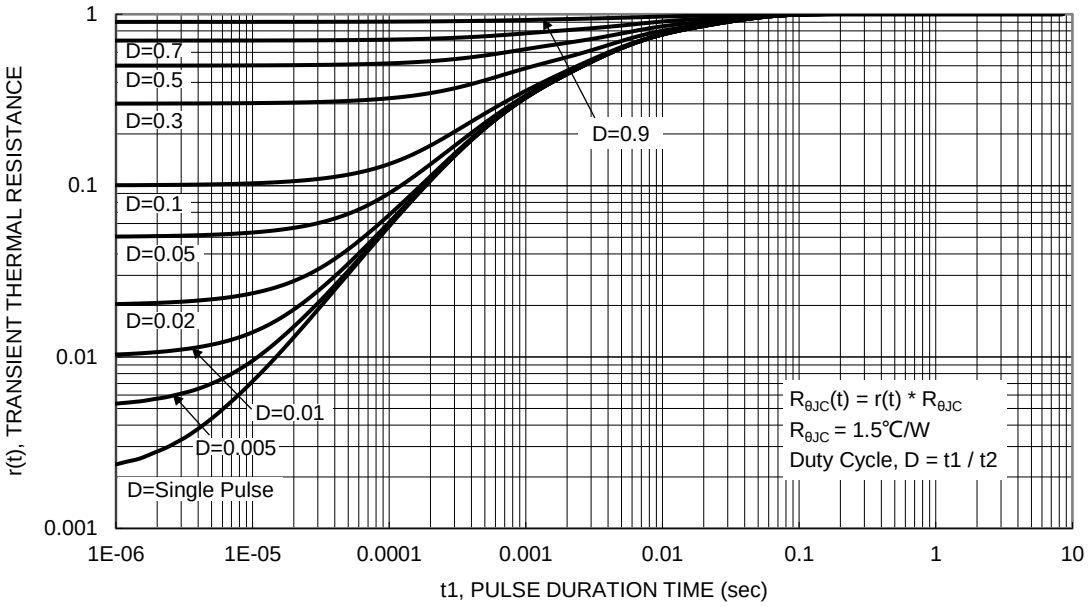
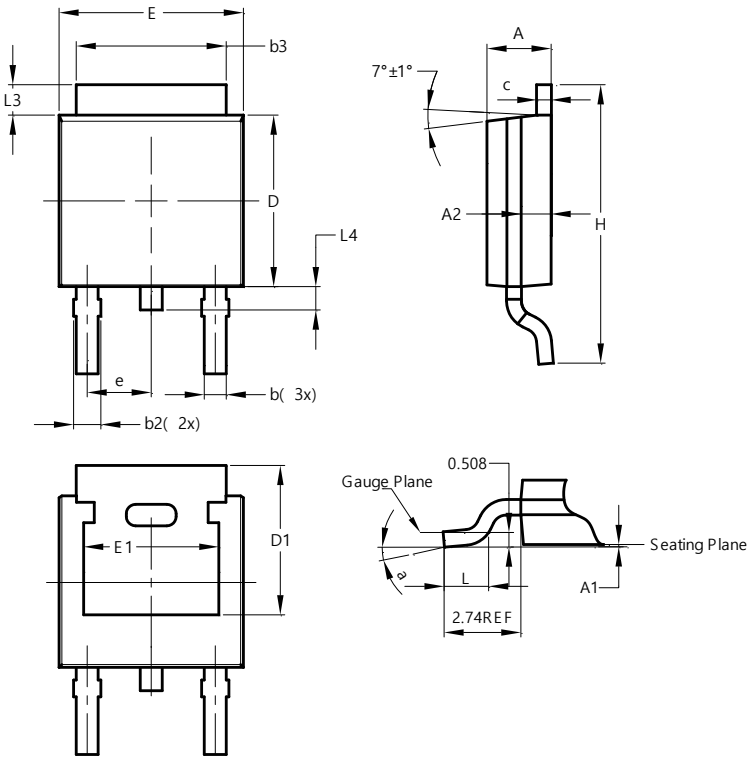


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

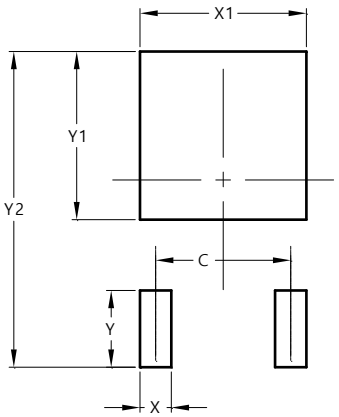
TO252 (DPAK)



TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700